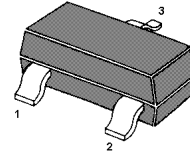


NPN Silicon Epitaxial Planar Transistor  
for switching and amplifier applications.

As complementary type the PNP transistor  
MMBT8550C and MMBT8550D are  
recommended.

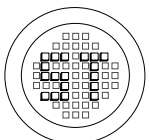


1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

	Symbol	Value	Unit
Collector Emitter Voltage	$V_{CEO}$	25	V
Collector Base Voltage	$V_{CBO}$	40	V
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	600	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_s$	-55 to +150	$^\circ\text{C}$



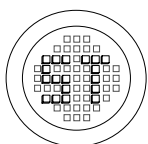
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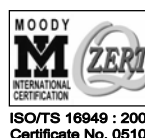
## Characteristics at T<sub>a</sub> = 25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V <sub>CE</sub> =1V, I <sub>C</sub> =100mA	MMBT8050C h <sub>FE</sub>	100	-	250	-
	MMBT8050D h <sub>FE</sub>	160	-	400	-
	at V <sub>CE</sub> =1V, I <sub>C</sub> =500mA h <sub>FE</sub>	40	-	-	-
Collector Cutoff Current at V <sub>CB</sub> =35V	I <sub>CBO</sub>	-	-	100	nA
Collector Saturation Voltage at I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	V <sub>CE(sat)</sub>	-	-	0.5	V
Base Saturation Voltage at I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	V <sub>BE(sat)</sub>	-	-	1.2	V
Collector Emitter Breakdown Voltage at I <sub>C</sub> =2mA	V <sub>(BR)CEO</sub>	25	-	-	V
Collector Base Breakdown Voltage at I <sub>C</sub> =10μA	V <sub>(BR)CBO</sub>	40	-	-	V
Emitter Base Breakdown Voltage at I <sub>E</sub> =100μA	V <sub>(BR)EBO</sub>	6	-	-	V
Gain Bandwidth Product at V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=50MHz	f <sub>T</sub>	-	100	-	MHz
Collector Base Capacitance at V <sub>CB</sub> =10V, f=1MHz	C <sub>CBO</sub>	-	12	-	pF
Thermal Resistance Junction to Ambient	R <sub>thA</sub>	-	-	200	K/W



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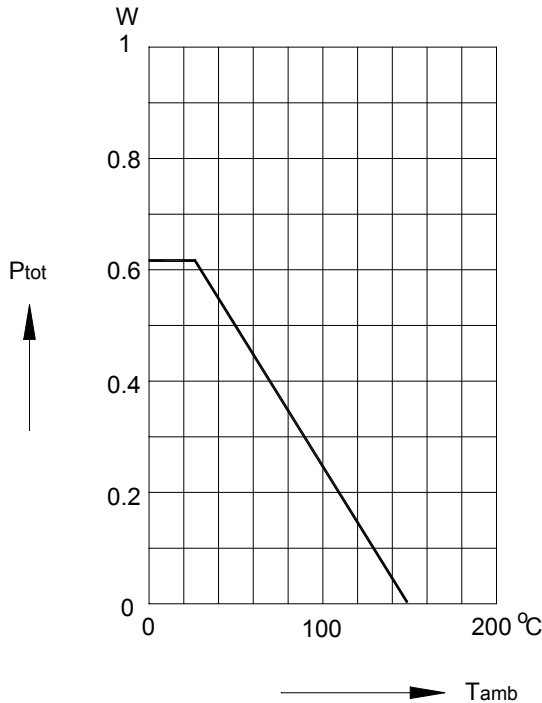
ISO/TS 16949 : 2002  
Certificate No. 05103

ISO 14001  
Certificate No. 05103

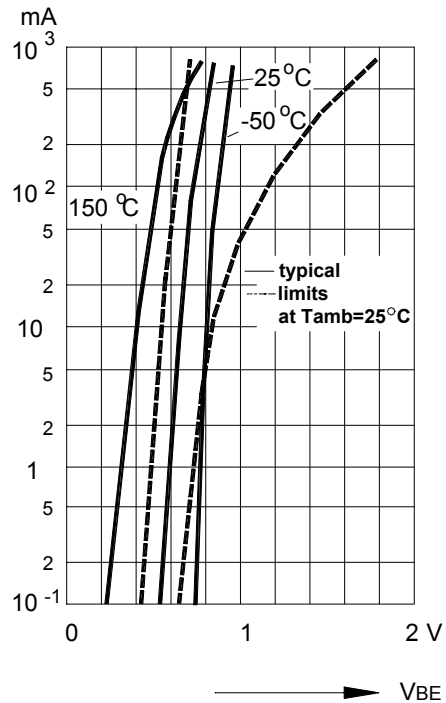
ISO 9001:2000  
Certificate No. 05103

**Admissible power dissipation versus ambient temperature**

Valid provided that leads are kept at ambient temperature at a distance of 2mm from case

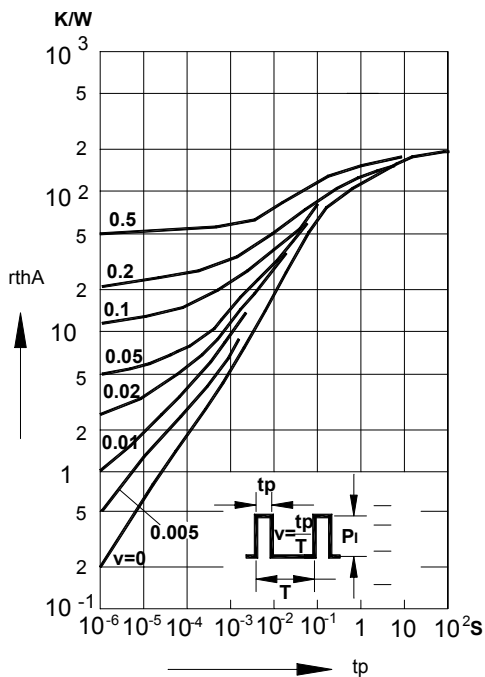


**Collector current versus base emitter voltage**

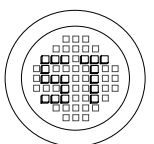
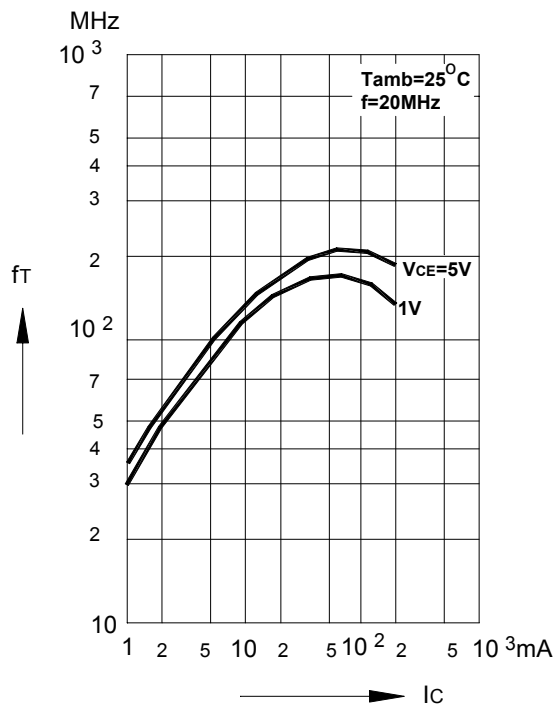


**Pulse thermal resistance versus pulse duration**

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

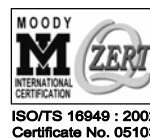


**Gain bandwidth product versus collector current**



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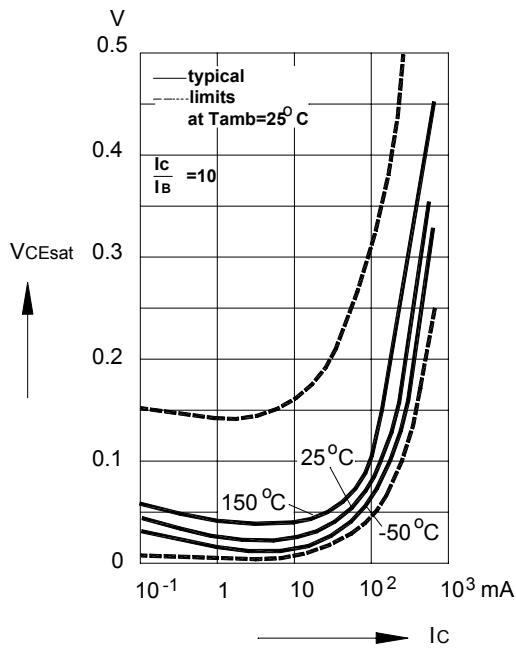
ISO/TS 16949 : 2002 Certificate No. 05103

ISO 14001 Certificate No. 05103

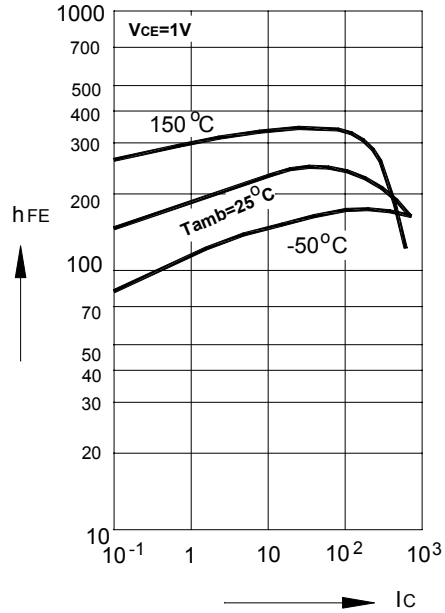
ISO 9001:2000 Certificate No. 05103

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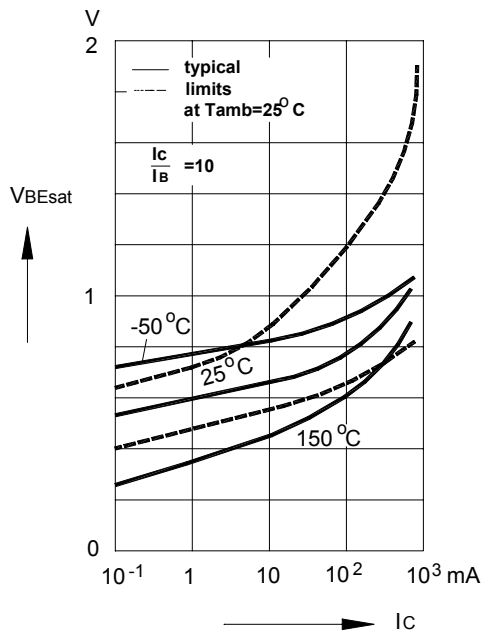
Collector saturation voltage versus collector current



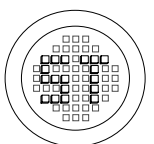
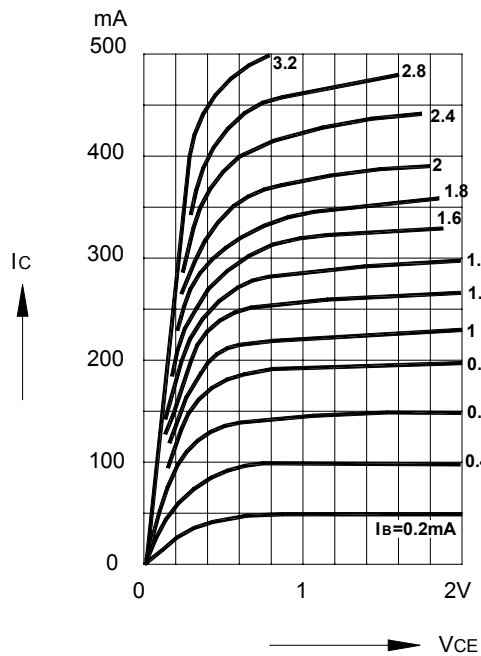
DC current gain versus collector current



Base saturation voltage versus collector current

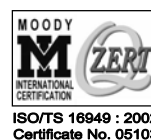


Common emitter collector characteristics

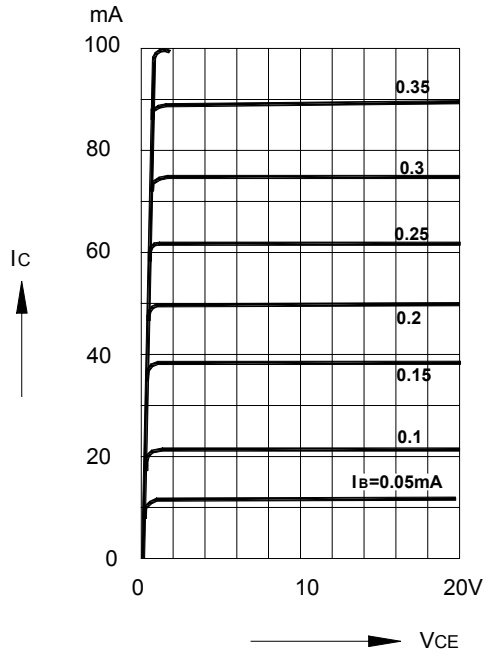


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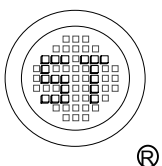
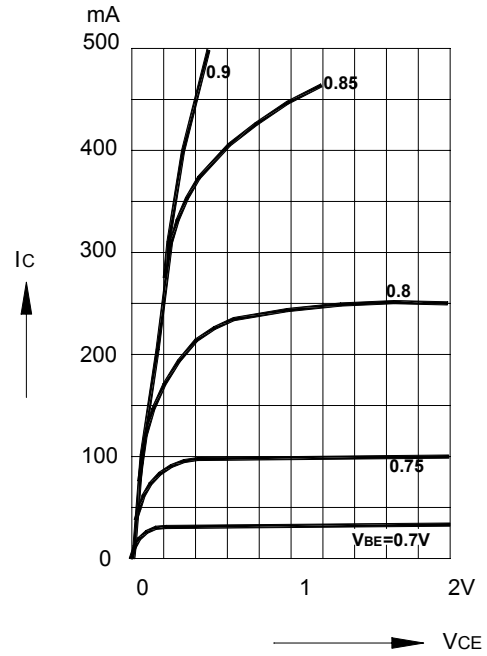
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Common emitter collector characteristics



Common emitter collector characteristics



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